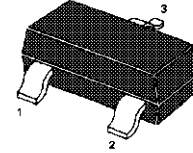


MMBT8550C / MMBT8550D (1.5A)

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into two groups, C and D, according to its DC current gain. As complementary type the NPN transistor MMBT8050C and MMBT8050D (1.5A) is recommended.

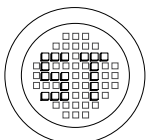


1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| | Symbol | Value | Unit |
|---------------------------|------------|-------------|------------------|
| Collector Emitter Voltage | $-V_{CEO}$ | 25 | V |
| Collector Base Voltage | $-V_{CBO}$ | 40 | V |
| Emitter Base Voltage | $-V_{EBO}$ | 6 | V |
| Peak Collector Current | $-I_{CM}$ | 1.5 | A |
| Power Dissipation | P_{tot} | 200 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_s | -55 to +150 | $^\circ\text{C}$ |



®

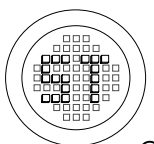
РАДИОТЕХ

Тел.: (495) 795-0805
Факс: (495) 234-1603
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Веб: www.rct.ru

MMBT8550C / MMBT8550D (1.5A)

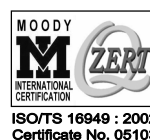
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

| | Symbol | Min. | Max. | Unit |
|--|-----------------------|------|------|------|
| DC Current Gain | | | | |
| at $-V_{CE}=1\text{V}$, $-I_C=100\text{mA}$ | MMBT8550C h_{FE} | 120 | 250 | - |
| | MMBT8550D h_{FE} | 160 | 400 | - |
| at $-V_{CE}=1\text{V}$, $-I_C=800\text{mA}$ | h_{FE} | 40 | - | - |
| Collector Cutoff Current | | | | |
| at $-V_{CB}=35\text{V}$ | $-I_{CBO}$ | - | 100 | nA |
| Emitter Cutoff Current | | | | |
| at $-V_{BE}=6\text{V}$ | $-I_{EBO}$ | - | 100 | nA |
| Collector Saturation Voltage | | | | |
| at $-I_C=800\text{mA}$, $-I_B=80\text{mA}$ | $-V_{CE(sat)}$ | - | 0.5 | V |
| Base Saturation Voltage | | | | |
| at $-I_C=800\text{mA}$, $-I_B=80\text{mA}$ | $-V_{BE(sat)}$ | - | 1.2 | V |
| Collector Emitter Breakdown Voltage | | | | |
| at $-I_C=2\text{mA}$ | $-V_{(BR)CEO}$ | 25 | - | V |
| Collector Base Breakdown Voltage | | | | |
| at $-I_C=100\mu\text{A}$ | $-V_{(BR)CBO}$ | 40 | - | V |
| Emitter Base Breakdown Voltage | | | | |
| at $-I_E=100\mu\text{A}$ | $-V_{(BR)EBO}$ | 6 | - | V |
| Base Emitter Voltage | | | | |
| at $-I_C=10\text{mA}$, $-V_{CE}=1\text{V}$ | $-V_{BE}$ | - | 1 | V |
| Gain Bandwidth Product | | | | |
| at $-V_{CE}=10\text{V}$, $-I_C=50\text{mA}$ | f_T | 120 | - | MHz |



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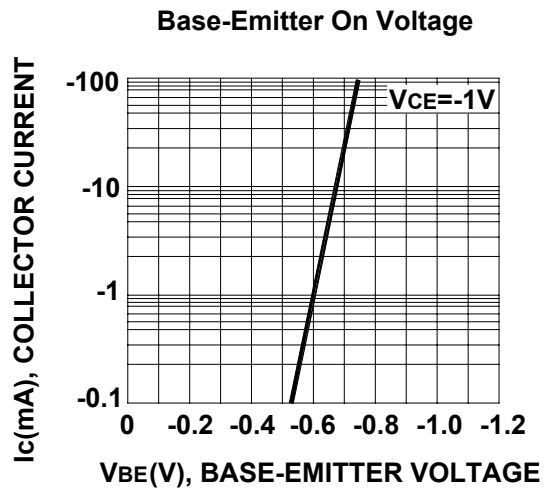
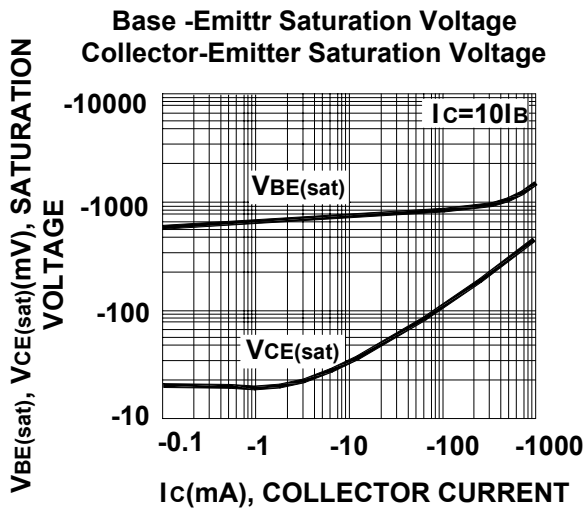
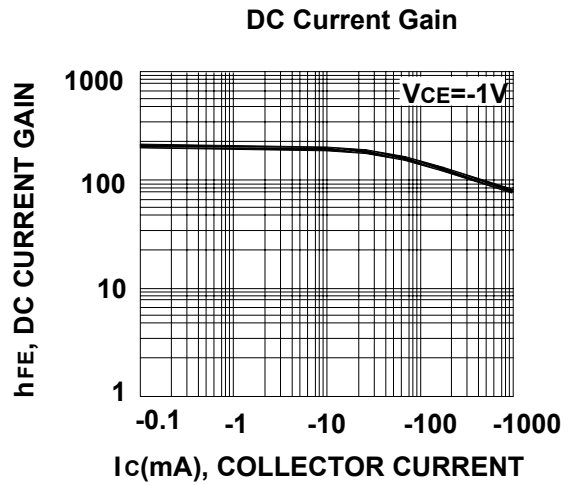
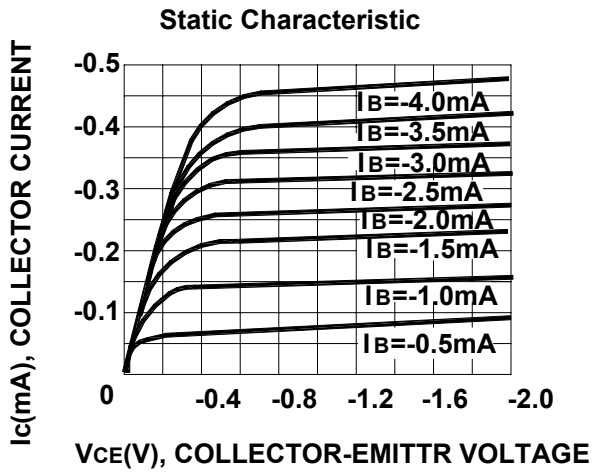
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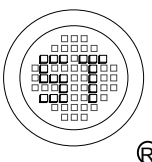
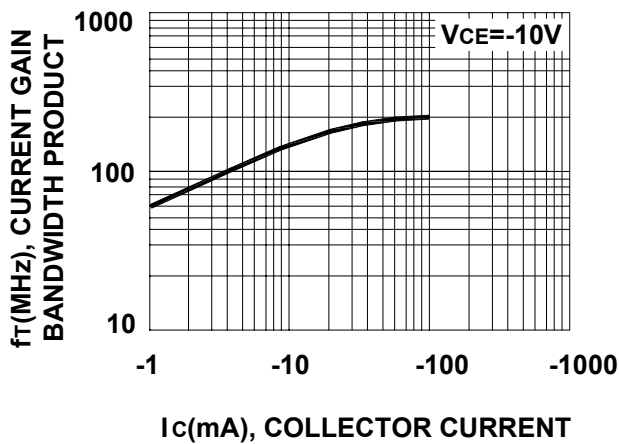
Dated : 20/10/2005

MMBT8550C / MMBT8550D (1.5A)

Typical Characteristics

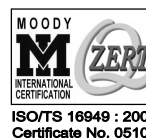


Current Gain Bandwidth Product



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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 5558-1986-AD-RSC-Pak

Dated : 20/10/2005